



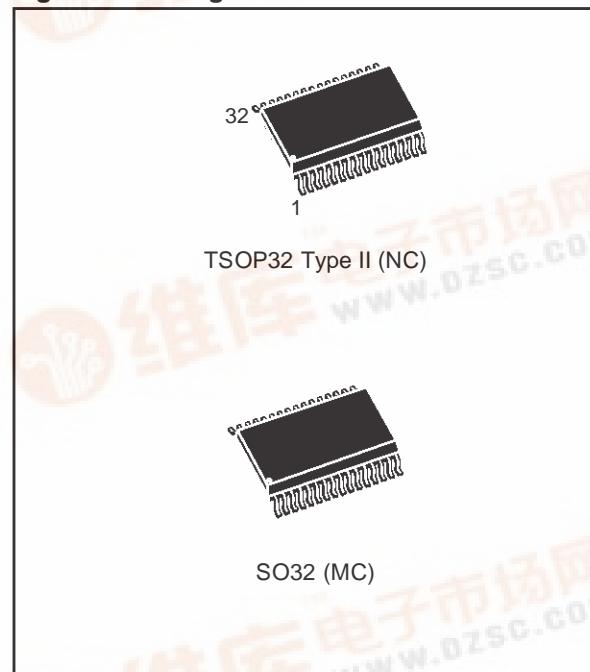
M68AF511AL

4 Mbit (512K x8), 5V Asynchronous SRAM

FEATURES SUMMARY

- SUPPLY VOLTAGE: 4.5 to 5.5V
- 512K x 8 bits SRAM with OUTPUT ENABLE
- EQUAL CYCLE and ACCESS TIMES: 55ns
- LOW STANDBY CURRENT
- LOW V_{CC} DATA RETENTION: 2V
- TRI-STATE COMMON I/O
- LOW ACTIVE and STANDBY POWER

Figure 1. Packages



M68AF511AL

TABLE OF CONTENTS

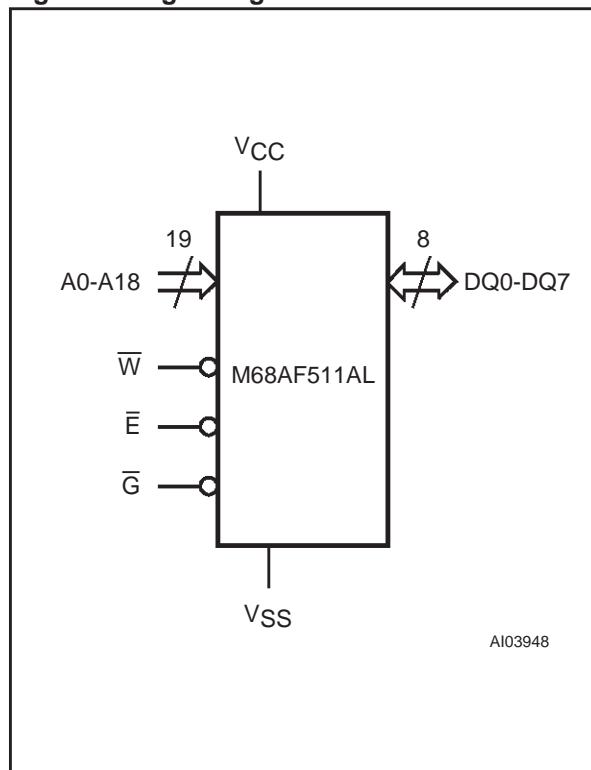
SUMMARY DESCRIPTION	3
Figure 2. Logic Diagram	3
Table 1. Signal Names	3
Figure 3. TSOP and SO Connections	4
Figure 4. Block Diagram	5
MAXIMUM RATING	5
Table 2. Absolute Maximum Ratings	5
DC AND AC PARAMETERS	6
Table 3. Operating and AC Measurement Conditions	6
Figure 5. AC Measurement I/O Waveform	6
Figure 6. AC Measurement Load Circuit	6
Table 4. Capacitance	7
Table 5. DC Characteristics	7
OPERATION	8
Table 6. Operating Modes	8
Read Mode	8
Figure 7. Address Controlled, Read Mode AC Waveforms	8
Figure 8. Chip Enable or Output Enable Controlled, Read Mode AC Waveforms	9
Table 7. Read and Standby Mode AC Characteristics	10
Write Mode	11
Figure 10. Write Enable Controlled, Write AC Waveforms	11
Figure 11. Chip Enable Controlled, Write AC Waveforms	12
Table 8. Write Mode AC Characteristics	12
Table 9. Low V _{CC} Data Retention Characteristics	13
PACKAGE MECHANICAL	14
TSOP 32 Type II - 32 lead Plastic Thin Small Outline Type II, Package Outline	14
TSOP 32 Type II - 32 lead Plastic Thin Small Outline Type II, Package Mechanical Data	14
SO32 - 32 lead Plastic Small Outline, Package Outline	15
SO32 - 32 lead Plastic Small Outline, Package Mechanical Data	15
PART NUMBERING	16
Table 12. Ordering Information Scheme	16
REVISION HISTORY	17
Table 13. Document Revision History	17

SUMMARY DESCRIPTION

The M68AF511AL is a 4 Mbit (4,194,304 bit) CMOS SRAM, organized as 524,288 words by 8 bits. The device features fully static operation requiring no external clocks or timing strobes, with equal address access and cycle times. It requires a single 4.5 to 5.5V supply.

This device has an automatic power-down feature, reducing the power consumption by over 99% when deselected.

The M68AF511AL is available in a 32 lead TSOP Type II and 32 lead SO packages.

Figure 2. Logic Diagram**Table 1. Signal Names**

A0-A18	Address Inputs
DQ0-DQ7	Data Input/Output
\bar{E}	Chip Enable
\bar{G}	Output Enable
\bar{W}	Write Enable
Vcc	Supply Voltage
Vss	Ground

M68AF511AL

Figure 3. TSOP and SO Connections

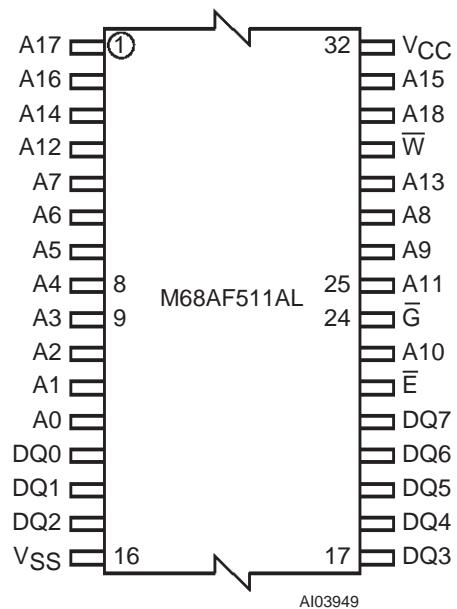
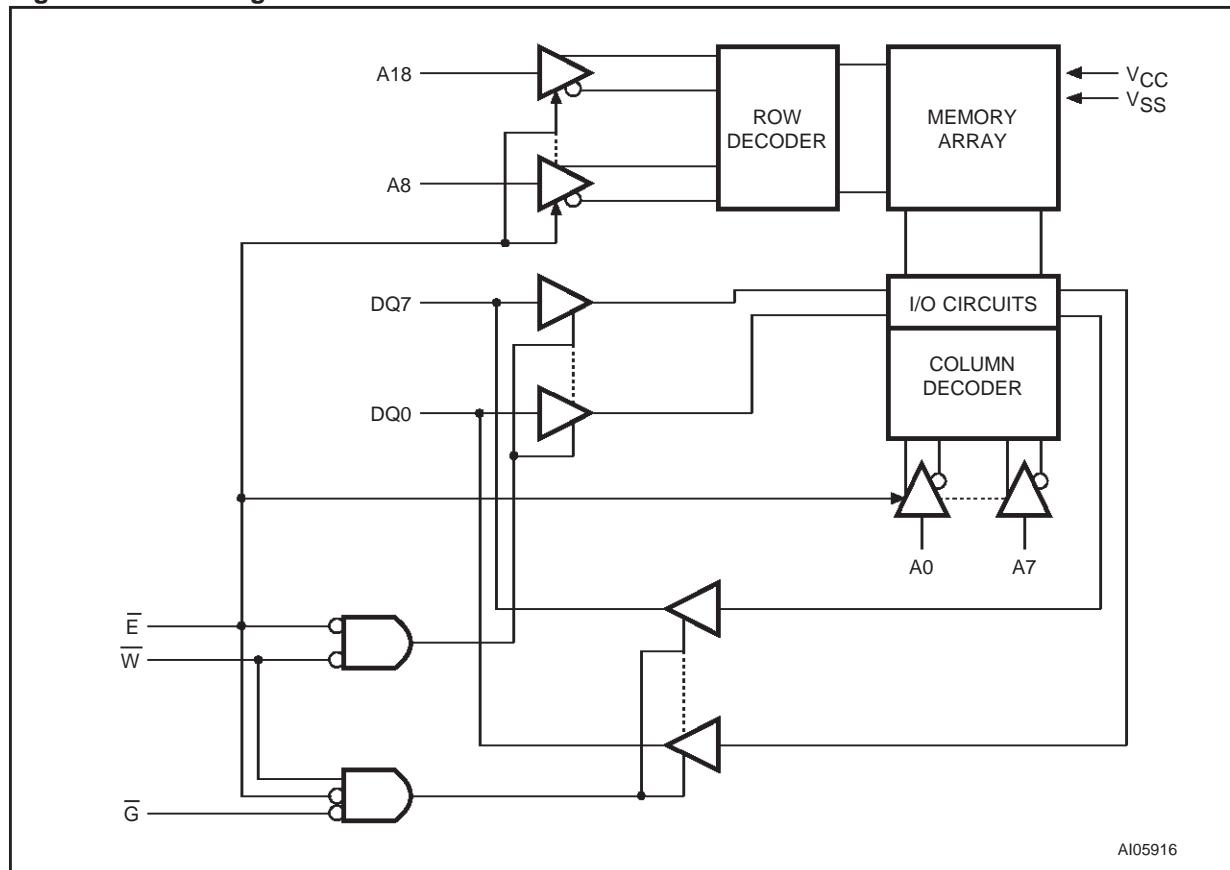


Figure 4. Block Diagram**MAXIMUM RATING**

Stressing the device above the rating listed in the Absolute Maximum Ratings table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not im-

plied. Exposure to Absolute Maximum Rating conditions for periods greater than 1 sec may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 2. Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
$I_O^{(1)}$	Output Current	20	mA
T_A	Ambient Operating Temperature	-55 to 125	°C
T_{STG}	Storage Temperature	-65 to 150	°C
V_{CC}	Supply Voltage	-0.5 to 6.5	V
$V_{IO}^{(2)}$	Input or Output Voltage	-0.5 to $V_{CC} + 0.5$	V
P_D	Power Dissipation	1	W

Note: 1. One output at a time, not to exceed 1 second duration.

2. Up to a maximum operating V_{CC} of 6.0V only.

M68AF511AL

DC AND AC PARAMETERS

This section summarizes the operating and measurement conditions, as well as the DC and AC characteristics of the device. The parameters in the following DC and AC Characteristic tables are derived from tests performed under the Measure-

ment Conditions listed in the relevant tables. Designers should check that the operating conditions in their projects match the measurement conditions when using the quoted parameters.

Table 3. Operating and AC Measurement Conditions

Parameter	M68AF511AL	
V _{CC} Supply Voltage	4.5 to 5.5V	
Ambient Operating Temperature	Range 1: Commercial	0 to 70°C
	Range 6: Industrial	-40 to 85°C
Load Capacitance (C _L)	100pF	
Output Circuit Protection Resistance (R ₁)	3.0kΩ	
Load Resistance (R ₂)	3.1kΩ	
Input Rise and Fall Times	1ns/V	
Input Pulse Voltages	0 to V _{CC}	
Input and Output Timing Ref. Voltages	V _{CC} /2	
Output Transition Timing Ref. Voltages	V _{RL} = 0.3V _{CC} ; V _{RH} = 0.7V _{CC}	

Figure 5. AC Measurement I/O Waveform

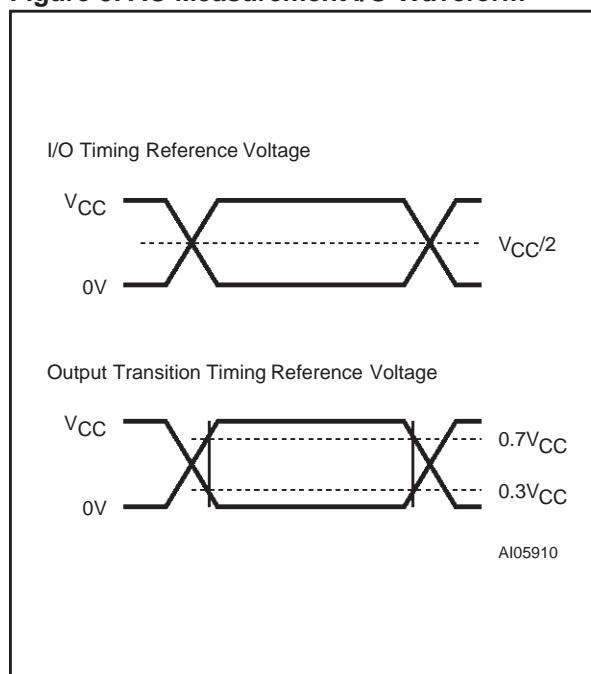


Figure 6. AC Measurement Load Circuit

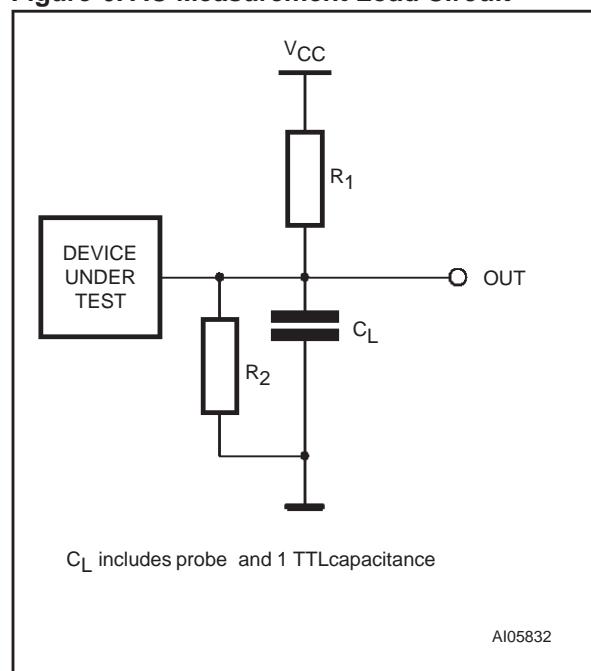


Table 4. Capacitance

Symbol	Parameter ^(1,2)	Test Condition	Min	Max	Unit
C _{IN}	Input Capacitance on all pins (except DQ)	V _{IN} = 0V		6	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V		8	pF

Note: 1. Sampled only, not 100% tested.
 2. At T_A = 25°C, f = 1MHz, V_{CC} = 5.0V.

Table 5. DC Characteristics

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
I _{CC1} ^(1,2)	Operating Supply Current	V _{CC} = 5.5V, f = 1/t _{AVAV} , I _{OUT} = 0mA			55	mA
I _{CC2} ⁽³⁾	Operating Supply Current	V _{CC} = 5.5V, f = 1MHz, I _{OUT} = 0mA			5	mA
I _{LI}	Input Leakage Current	0V ≤ V _{IN} ≤ V _{CC}	-1		1	µA
I _{LO} ⁽⁴⁾	Output Leakage Current	0V ≤ V _{OUT} ≤ V _{CC}	-1		1	µA
I _{SB}	Standby Supply Current CMOS	V _{CC} = 5.5V, Ē ≥ V _{CC} - 0.2V, f = 0		5	10	µA
V _{IH}	Input High Voltage		2.2		V _{CC} + 0.3	V
V _{IL}	Input Low Voltage		-0.3		0.8	V
V _{OH}	Output High Voltage	I _{OH} = -1.0mA	2.4			V
V _{OL}	Output Low Voltage	I _{OL} = 2.1mA			0.4	V

Note: 1. Average AC current, cycling at t_{AVAV} minimum.
 2. Ē = V_{IL}, V_{IN} = V_{IH} or V_{IL}.
 3. Ē ≤ 0.2V, V_{IN} ≤ 0.2V or V_{IN} ≥ V_{CC} - 0.2V.
 4. Output disable.

M68AF511AL

OPERATION

The M68AF511AL has a Chip Enable power down feature which invokes an automatic standby mode whenever Chip Enable is de-asserted (\bar{E} = High). An Output Enable (G) signal provides a high speed tri-state control, allowing fast read/write cy-

cles to be achieved with the common I/O data bus. Operational modes are determined by device control inputs W and E as summarized in the Operating Modes table (Table 6).

Table 6. Operating Modes

Operation	\bar{E}	\bar{W}	\bar{G}	DQ0-DQ7	Power
Output disabled	V_{IL}	X	V_{IH}	Hi-Z	Active (Icc)
Read	V_{IL}	V_{IH}	V_{IL}	Data Output	Active (Icc)
Write	V_{IL}	V_{IL}	X	Data Input	Active (Icc)
Deselect	V_{IH}	X	X	Hi-Z	Standby (Isb)

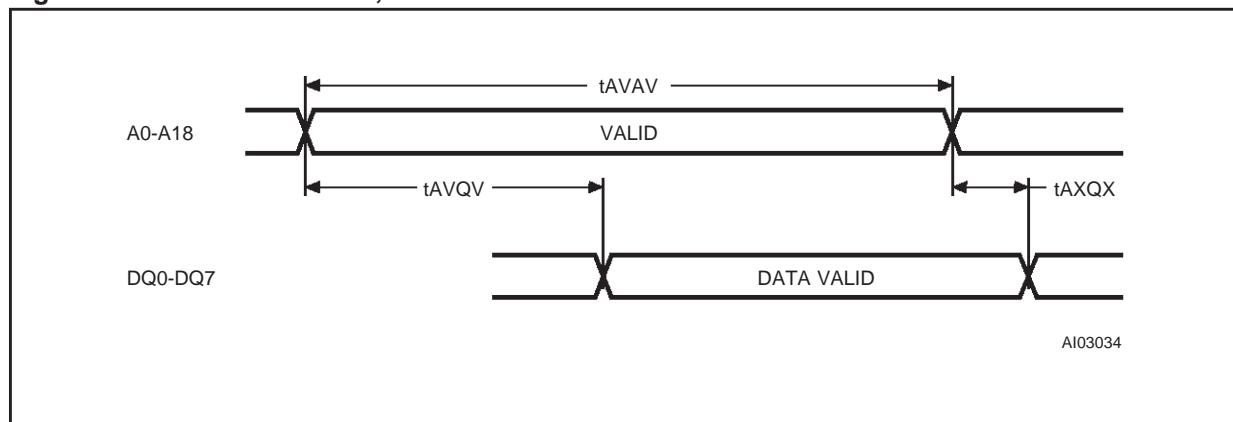
Note: X = V_{IH} or V_{IL} .

Read Mode

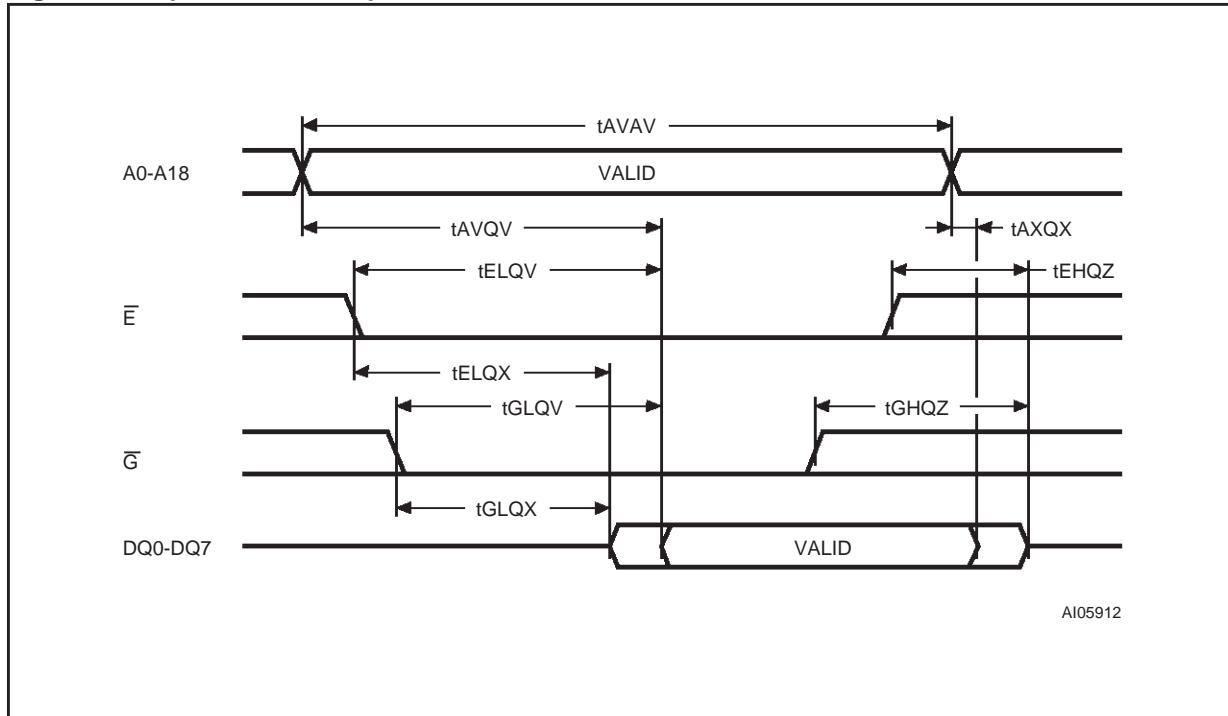
The M68AF511AL is in the Read mode whenever Write Enable (W) is High with Output Enable (G) Low, and Chip Enable (\bar{E}) is asserted. This provides access to data from eight of the 4,194,304 locations in the static memory array, specified by the 19 address inputs. Valid data will be available at the eight output pins within t_{AVQV} after the last

stable address, providing \bar{G} is Low and \bar{E} is Low. If Chip Enable or Output Enable access times are not met, data access will be measured from the limiting parameter (t_{ELQV} or t_{GLQV}) rather than the address. Data out may be indeterminate at t_{ELQX} and t_{GLQX} , but data lines will always be valid at t_{AVQV} .

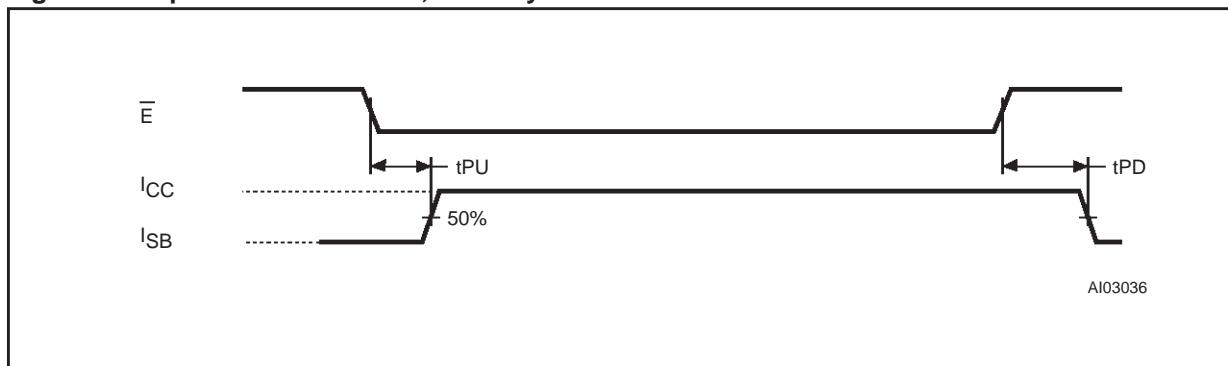
Figure 7. Address Controlled, Read Mode AC Waveforms



Note: \bar{E} = Low, \bar{G} = Low, \bar{W} = High.

Figure 8. Chip Enable or Output Enable Controlled, Read Mode AC Waveforms.

Note: Write Enable (\overline{W}) = High.

Figure 9. Chip Enable Controlled, Standby Mode AC Waveforms

M68AF511AL

Table 7. Read and Standby Mode AC Characteristics

Symbol	Parameter	M68AF511AL			Unit
			55	70	
tAVAV	Read Cycle Time	Min	55	70	ns
tAVQV	Address Valid to Output Valid	Max	55	70	ns
tAXQX ⁽¹⁾	Data hold from Address change	Min	5	5	ns
tEHQZ ^(2,3)	Chip Enable High to Output Hi-Z	Max	20	25	ns
tELQV	Chip Enable Low to Output Valid	Max	55	70	ns
tELQX ⁽¹⁾	Chip Enable Low to Output Transition	Min	5	5	ns
tGHQZ ^(2,3)	Output Enable High to Output Hi-Z	Max	20	25	ns
tGLQV	Output Enable Low to Output Valid	Max	25	35	ns
tGLQX ⁽¹⁾	Output Enable Low to Output Transition	Min	5	5	ns
tPD ⁽⁴⁾	Chip Enable High to Power Down	Max	0	0	ns
tPU ⁽⁴⁾	Chip Enable Low to Power Up	Min	55	70	ns

Note:

1. Test conditions assume transition timing reference level = 0.3V_{CC} or 0.7V_{CC}.
2. At any given temperature and voltage condition, tEHQZ is less than tELQX and tGHQZ is less than tGLQX for any given device.
3. These parameters are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
4. Tested initially and after any design or process changes that may affect these parameters

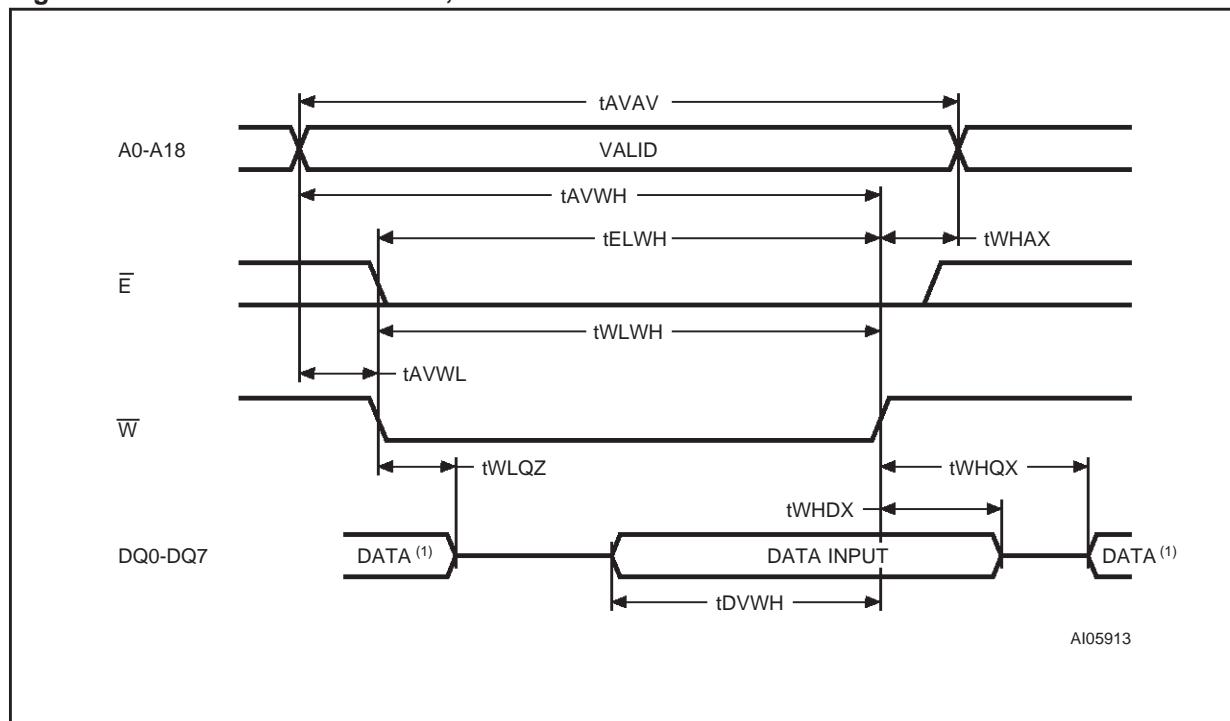
Write Mode

The M68AF511AL is in the Write mode whenever the \bar{W} and \bar{E} pins are Low. Either the Chip Enable input (\bar{E}) or the Write Enable input (\bar{W}) must be deasserted during Address transitions for subsequent write cycles. Write begins with the concurrence of Chip Enable being active with \bar{W} low. Therefore, address setup time is referenced to Write Enable and Chip Enable as t_{AVWL} and t_{AVEH} respectively, and is determined by the latter occurring edge.

The Write cycle can be terminated by the earlier rising edge of \bar{E} , or \bar{W} .

If the Output is enabled (\bar{E} = Low and \bar{G} = Low), then \bar{W} will return the outputs to high impedance within t_{WLQZ} of its falling edge. Care must be taken to avoid bus contention in this type of operation. Data input must be valid for t_{DVWH} before the rising edge of Write Enable, or for t_{DVEH} before the rising edge of \bar{E} , whichever occurs first, and remain valid for t_{WHDX} or t_{EHDX} .

Figure 10. Write Enable Controlled, Write AC Waveforms



Note: 1. During this period DQ0-DQ7 are in output state and input signal should not be applied.

M68AF511AL

Figure 11. Chip Enable Controlled, Write AC Waveforms

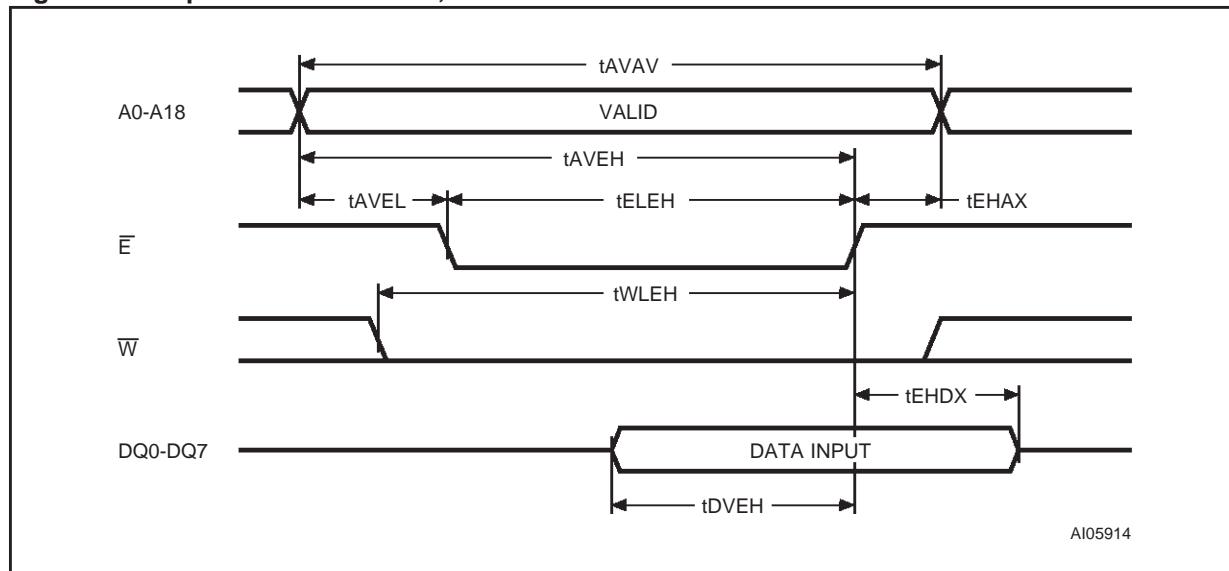
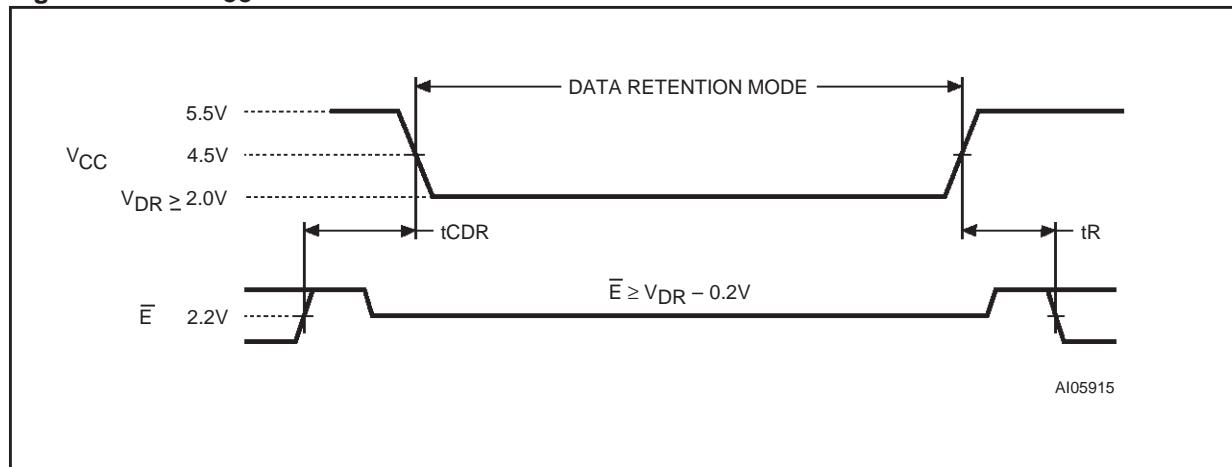


Table 8. Write Mode AC Characteristics

Symbol	Parameter	M68AF511AL			Unit
			55	70	
tAVAV	Write Cycle Time	Min	55	70	ns
tAVEH	Address Valid to Chip Enable High	Min	45	60	ns
tAVEL	Address Valid to Chip Enable Low	Min	0	0	ns
tAVWH	Address Valid to Write Enable High	Min	45	60	ns
tAVWL	Address Valid to Write Enable Low	Min	0	0	ns
tDVEH	Input Valid to Chip Enable High	Min	25	30	ns
tDVWH	Input Valid to Write Enable High	Min	25	30	ns
tEHAX	Chip Enable High to Address Transition	Min	0	0	ns
tEHDX	Chip Enable High to Input Transition	Min	0	0	ns
tELEH	Chip Enable Low to Chip Enable High	Min	45	60	ns
tELWH	Chip Enable Low to Write Enable High	Min	45	60	ns
tWLEH	Write Enable Low to Chip Enable High	Min	45	60	ns
tWLQZ ^(1,2)	Write Enable Low to Output Hi-Z	Max	20	25	ns
tWLWH	Write Enable Low to Write Enable High	Min	45	60	ns

Note: 1. These parameters are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.

2. At any given temperature and voltage condition, tWLQZ is less than tWHQX for any given device.

Figure 12. Low V_{CC} Data Retention AC Waveforms.**Table 9. Low V_{CC} Data Retention Characteristics**

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
I _{CCDR} ⁽¹⁾	Supply Current (Data Retention)	V _{CC} = 2V, $\bar{E} \geq V_{CC} - 0.2V$, f = 0 ⁽³⁾		4.5	9	µA
t _{CDR} ^(1,2)	Chip Deselected to Data Retention Time		0			ns
t _R ⁽²⁾	Operation Recovery Time		t _{AVAV}			ns
V _{DR} ⁽²⁾	Supply Voltage (Data Retention)	$\bar{E} \geq V_{CC} - 0.2V$, f = 0	2			V

Note: 1. All other Inputs at $V_{IH} \geq V_{CC} - 0.2V$ or $V_{IL} \leq 0.2V$.

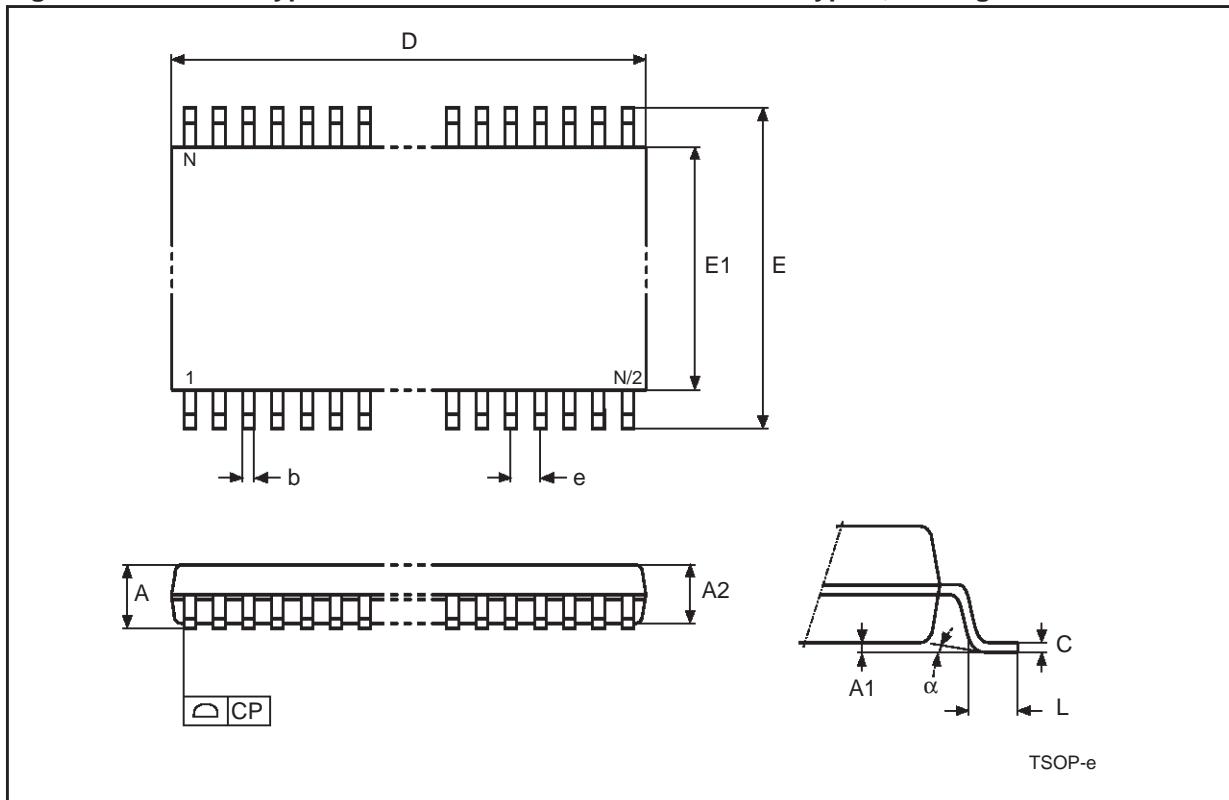
2. Tested initially and after any design or process that may affect these parameters. t_{AVAV} is Read cycle time.

3. No input may exceed V_{CC} +0.2V.

M68AF511AL

PACKAGE MECHANICAL

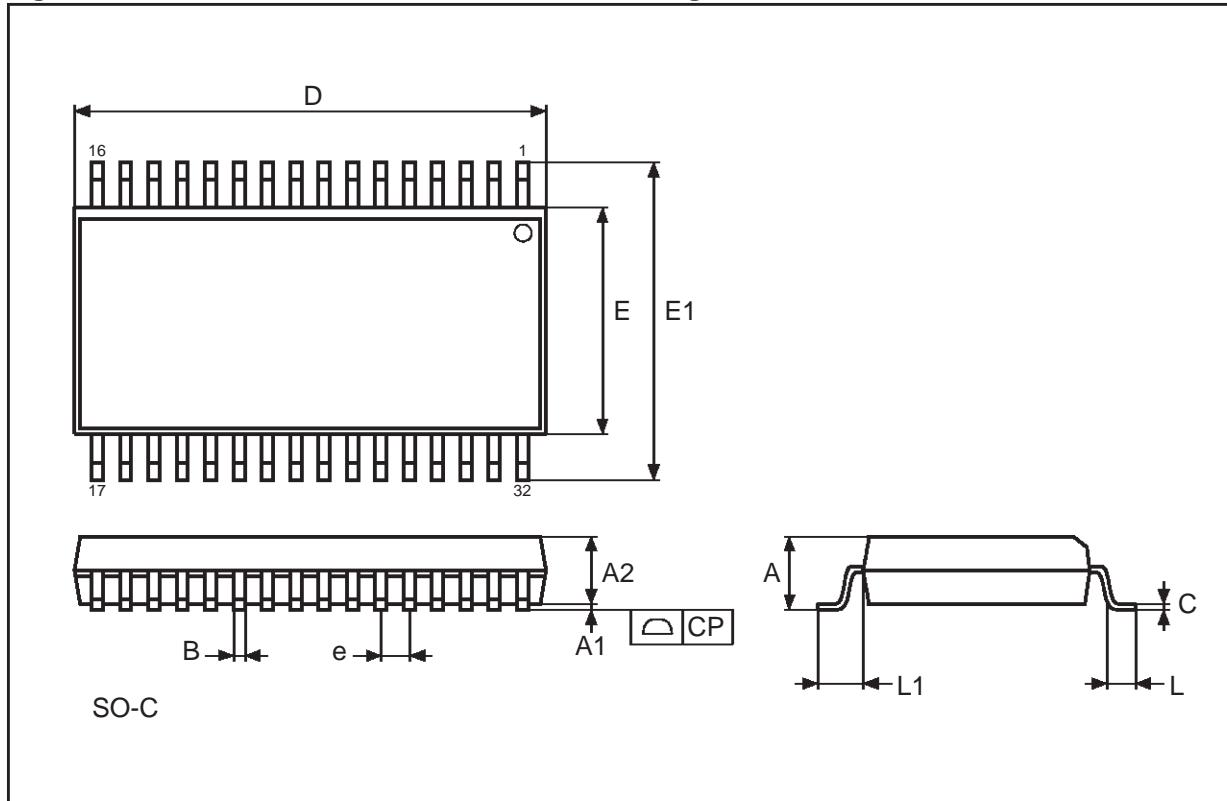
Figure 13. TSOP 32 Type II - 32 lead Plastic Thin Small Outline Type II, Package Outline



Note: Drawing is not to scale.

Table 10. TSOP 32 Type II - 32 lead Plastic Thin Small Outline Type II, Package Mechanical Data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A			1.20			0.047
A1		0.05	0.15		0.002	0.006
A2		0.95	1.05		0.037	0.041
b		0.30	0.52		0.012	0.020
C		0.12	0.21		0.005	0.008
CP			0.10			0.004
D		20.82	21.08		0.820	0.830
e	1.27	—	—	0.050	—	—
E		11.56	11.96		0.455	0.471
E1		10.03	10.29		0.395	0.405
L		0.40	0.60		0.016	0.024
α		0°	5°		0°	5°
N		32			32	

Figure 14. SO32 - 32 lead Plastic Small Outline, Package Outline

Note: Drawing is not to scale.

Table 11. SO32 - 32 lead Plastic Small Outline, Package Mechanical Data

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A			3.00			0.118
A1		0.10			0.004	
A2		2.57	2.82		0.101	0.111
B		0.36	0.51		0.014	0.020
C		0.15	0.30		0.006	0.012
D		20.14	20.75		0.793	0.817
E		11.18	11.43		0.440	0.450
E1		13.87	14.38		0.546	0.566
e	1.27	—	—	0.050	—	—
L		0.58	0.99		0.023	0.039
L1		1.19	1.60		0.047	0.063
CP			0.10			0.004

M68AF511AL

PART NUMBERING

Table 12. Ordering Information Scheme

Example:

Device Type

M68

Mode

A = Asynchronous

Operating Voltage

F = 4.5V to 5.5V

Array Organization

511 = 4 Mbit (512K x8)

Option 1

A = 1 Chip Enable

Option 2

L = Low leakage

Speed Class

55 = 55ns

70 = 70 ns

Package

NC = TSOP32 Type II

MC = SO32

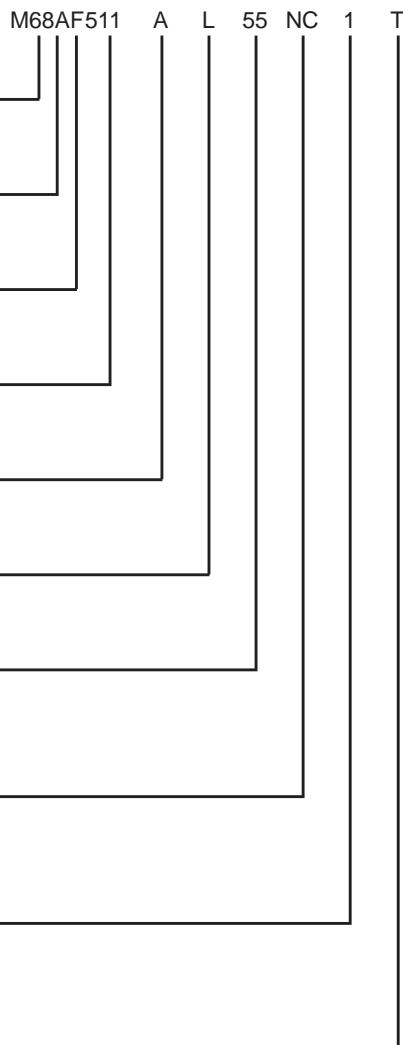
Operative Temperature

1 = 0 to 70 °C

6 = -40 to 85 °C

Shipping

T = Tape & Reel Packing



For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.

REVISION HISTORY**Table 13. Document Revision History**

Date	Version	Revision Details
July 2001	-01	First Issue
08-Aug-2001	-02	SO32 Package added 55ns Speed class introduced Industrial Temperature Range added (Range 6)
27-Sep-2001	-03	Typing error, Table 4, Note 2
18-Oct-2001	-04	SO32 Package Mechanical and Data added
29-Nov-2001	-05	Note Removed from Ordering Information Scheme
08-Jan-2002	-06	PDIP32 package added Document fully revised
08-Feb-2002	-07	t_{ELQX} , t_{AXQX} changed in Read and Standby Mode AC Characteristics Table (Table 7) t_{DVEH} , t_{DVWH} , t_{WLWH} changed in Write Mode AC Characteristics Table (Table 8)
25-Feb-2002	-08	PDIP32 package removed Block Diagram clarified (Figure 4) Absolute Maximum Ratings table clarified (Table 2) Operating and AC Measurement Conditions table and figure clarified (Table 3, Figure 6) DC Characteristics table clarified (Table 5) Read and Standby Mode AC Characteristics table clarified (Table 7) Write Mode AC Characteristics table clarified (Table 8)
03-Mar-2002	-09	Operating and AC Measurement Conditions table clarified (Table 3) I_{CCDR} Test Condition clarified (Table 9)
25-Mar-2002	-10	Read and Standby Mode AC Characteristics clarified (Table 7) Low V_{CC} Data Retention Characteristics clarified (Table 9)
18-Apr-2002	-11	Read and Standby Mode AC Characteristics (Table 7): t_{PD} and t_{PU} clarified
26-Apr-2002	-12	DC Characteristics Table clarified (Table 5) Write Mode AC Characteristics Table clarified (Table 8)
17-May-2002	-13	I_{SB} and I_{CCDR} values clarified

M68AF511AL

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